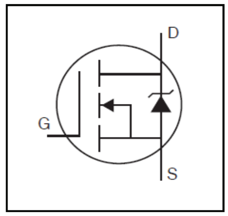
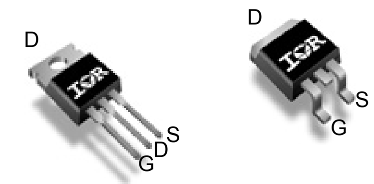
HEXFET® Power MOSFET

Features

- Advanced Process Technology
- Ultra Low On-Resistance
- Enhanced dV/dT and dI/dT capability
- 175°C Operating Temperature
- Fast Switching
- Repetitive Avalanche Allowed up to Tjmax
- Lead-Free, RoHS Compliant
- Automotive Qualified *



V_{DSS}	100V
$R_{DS(on)}$ typ.	11mΩ
max.	14mΩ
I_D	73A



TO-220
AUIRFB4610

D²Pak
AUIRFS4610

G	D	S
Gate	Drain	Source

Description

Specifically designed for Automotive applications, this HEXFET® Power MOSFET utilizes the latest processing techniques to achieve extremely low on-resistance per silicon area. Additional features of this design are a 175°C junction operating temperature, fast switching speed and improved repetitive avalanche rating . These features combine to make this design an extremely efficient and reliable device for use in Automotive applications and a wide variety of other applications

Base part number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
AUIRFB4610	TO-220	Tube	50	AUIRFB4610
AUIRFS4610	D²-Pak	Tube	50	AUIRFS4610
		Tape and Reel Left	800	AUIRFS4610TRL

Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (TA) is 25°C, unless otherwise specified.

Symbol	Parameter	Max.	Units
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V	73	A
I_D @ T_C = 100°C	Continuous Drain Current, V_{GS} @ 10V	52	
I_{DM}	Pulsed Drain Current ①	290	
P_D @T_C = 25°C	Maximum Power Dissipation	190	W
	Linear Derating Factor	1.3	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy (Thermally Limited) ②	370	mJ
I_{AR}	Avalanche Current ①	See Fig.14,15, 22a, 22b	A
E_{AR}	Repetitive Avalanche Energy ①		mJ
dv/dt	Peak Diode Recovery ③	7.6	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 175	°C
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	
	Mounting torque, 6-32 or M3 screw	10 lbf•in (1.1N•m)	

Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ⑧	——	0.77	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.50	——	
$R_{\theta JA}$	Junction-to-Ambient	——	62	
$R_{\theta JA}$	Junction-to-Ambient (PCB Mount, steady state) ⑦		40	

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*Qualification standards can be found at www.infineon.com

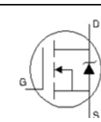
Static @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	100	—	—	V	V_{GS} = 0V, I_D = 250µA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.085	—	V/°C	Reference to 25°C, I_D = 1mA ①
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	11	14	mΩ	V_{GS} = 10V, I_D = 44A ④
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	V_{DS} = V_{GS}, I_D = 100µA
gfs	Forward Trans conductance	73	—	—	S	V_{DS} = 50V, I_D = 44A
R_G	Gate Resistance	—	1.5	—	Ω	f = 1.0MHz, open drain
I_{DSS}	Drain-to-Source Leakage Current	—	—	20	µA	V_{DS} = 100V, V_{GS} = 0V
		—	—	250		V_{DS} = 100V,V_{GS} = 0V,T_J =125°C
I_{GSS}	Gate-to-Source Forward Leakage	—	—	200	nA	V_{GS} = 20V
	Gate-to-Source Reverse Leakage	—	—	-200		V_{GS} = -20V

Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

Q_g	Total Gate Charge	—	90	140	nC	I_D = 44A
Q_{gs}	Gate-to-Source Charge	—	20	—		V_{DS} = 80V
Q_{gd}	Gate-to-Drain Charge	—	36	—		V_{GS} = 10V④
$t_{d(on)}$	Turn-On Delay Time	—	18	—	ns	V_{DD} = 65V
t_r	Rise Time	—	87	—		I_D = 44A
$t_{d(off)}$	Turn-Off Delay Time	—	53	—		R_G= 5.6Ω
t_f	Fall Time	—	70	—		V_{GS} = 10V④
C_{iss}	Input Capacitance	—	3550	—	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	—	260	—		V_{DS} = 50V
C_{rss}	Reverse Transfer Capacitance	—	150	—		f = 1.0MHz, See Fig. 5
$C_{oss\ eff.(ER)}$	Effective Output Capacitance (Energy Related)	—	330	—		V_{GS} = 0V, V_{DS} = 0V to 80V⑥
$C_{oss\ eff.(TR)}$	Effective Output Capacitance (Time Related)	—	380	—		V_{GS} = 0V, V_{DS} = 0V to 80V⑤

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	73	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ②	—	—	290		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	T_J = 25°C,I_S = 44A,V_{GS} = 0V ④
t_{rr}	Reverse Recovery Time	—	35	53	ns	T_J = 25°C V_{DD} = 85V
		—	42	63		T_J = 125°C I_F = 44A,
Q_{rr}	Reverse Recovery Charge	—	44	66	nC	T_J = 25°C di/dt = 100A/µs ④
		—	65	98		T_J = 125°C
I_{RRM}	Reverse Recovery Current	—	2.1	—	A	T_J = 25°C
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

Notes:

① Repetitive rating; pulse width limited by max. junction temperature.
② Limited by T_{Jmax}, starting T_J = 25°C, L = 0.39mH, R_G = 25Ω, I_{AS} = 44A, V_{GS} =10V. Part not recommended for use above this value.
③ $I_{SD} \leq$ 44A, di/dt ≤ 660A/µs, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq$ 175°C.
④ Pulse width ≤ 400µs; duty cycle ≤ 2%.
⑤ C_{oss} eff. (TR) is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.
⑥ C_{oss} eff. (ER) is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.
⑦ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994
⑧ R_θ is measured at T_J approximately 90°C.

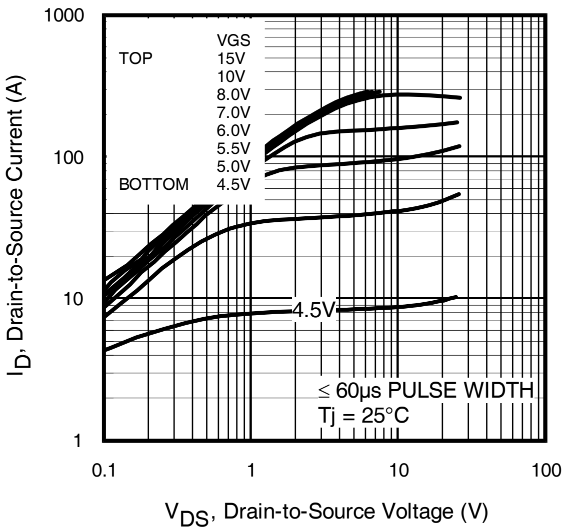


Fig. 1 Typical Output Characteristics

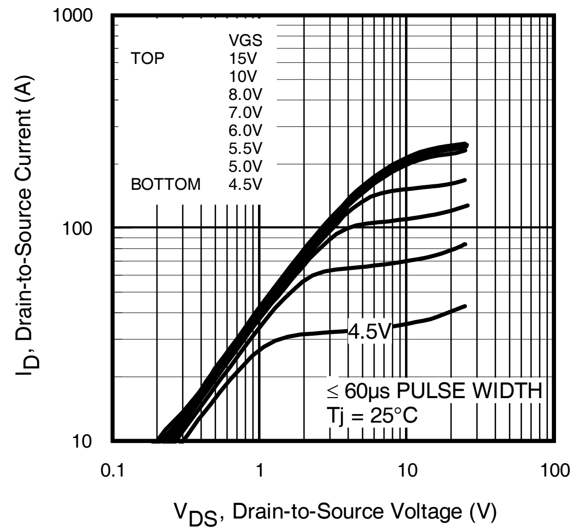


Fig. 2 Typical Output Characteristics

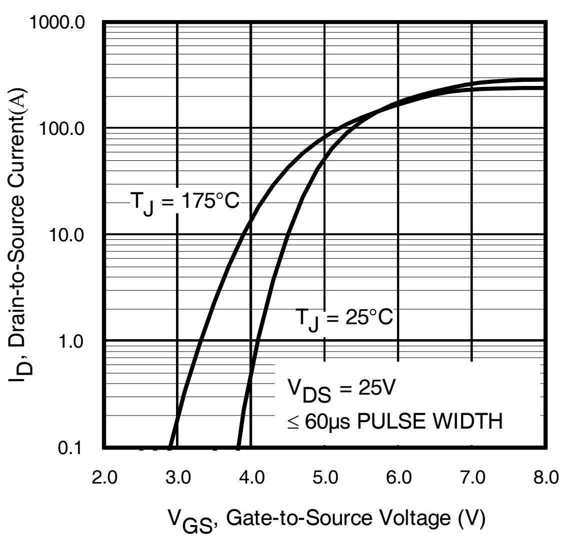


Fig. 3 Typical Transfer Characteristics

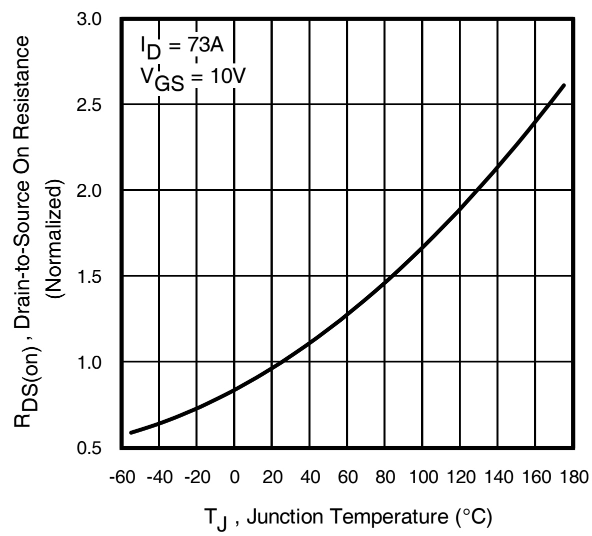


Fig. 4 Normalized On-Resistance vs. Temperature

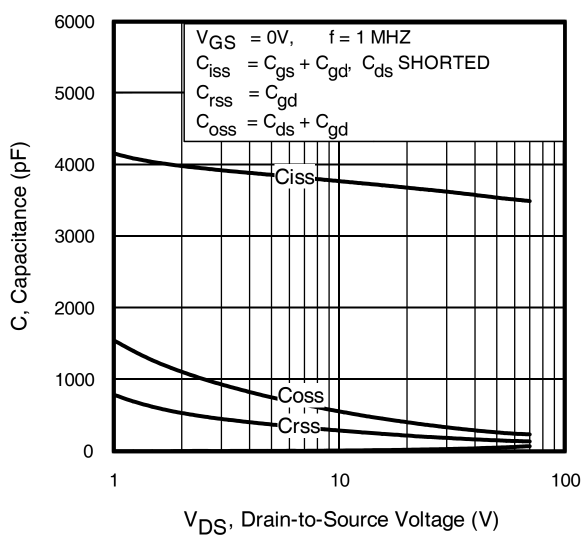


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

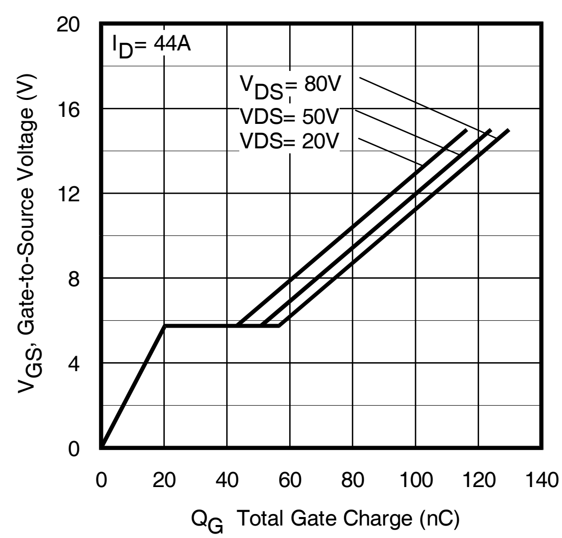


Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

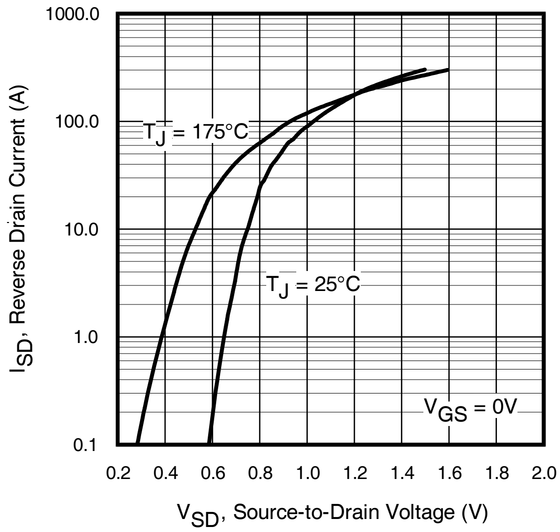


Fig. 7 Typical Source-to-Drain Diode Forward Voltage

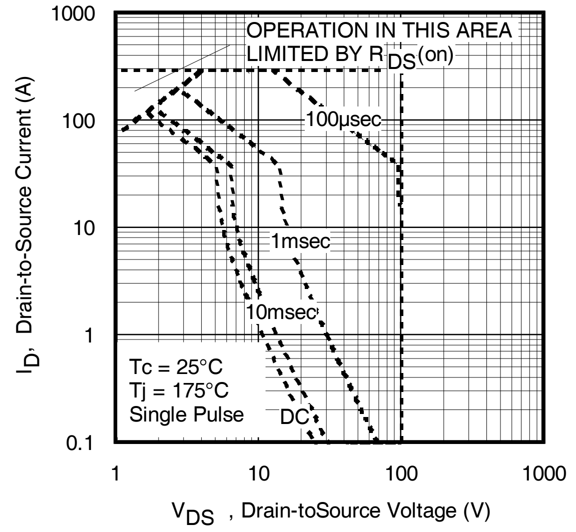
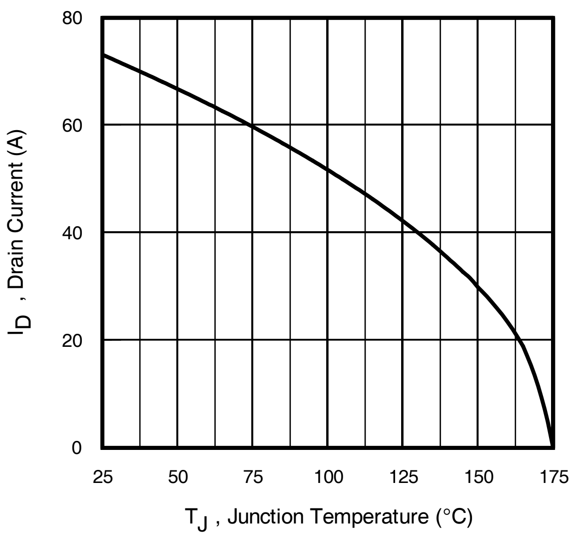


Fig 8. Maximum Safe Operating Area



Fg 9. Maximum Drain Current vs. Case Temperature

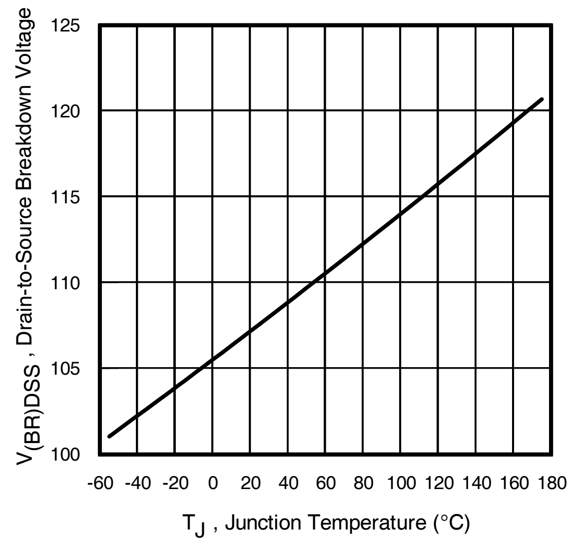


Fig 10. Drain-to-Source Breakdown Voltage

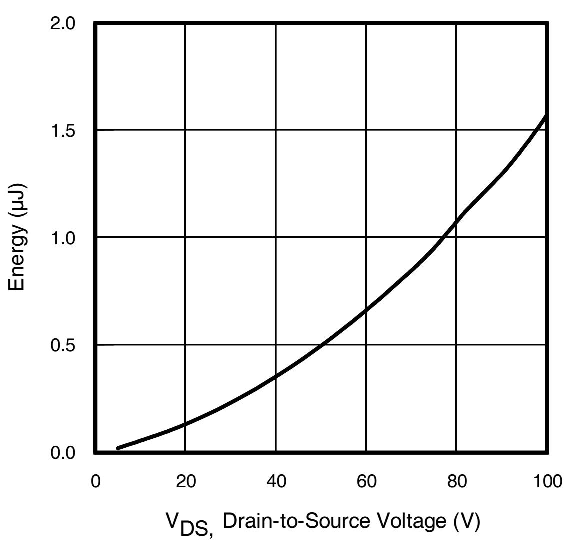


Fig 11. Typical Coss Stored Energy

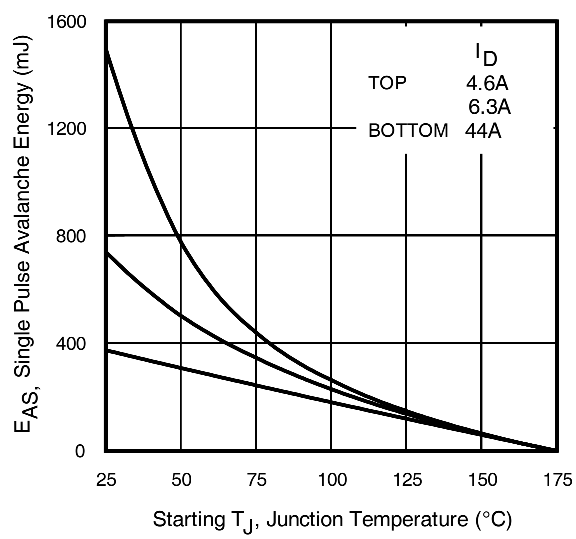


Fig 12. Maximum Avalanche Energy vs. Drain Current

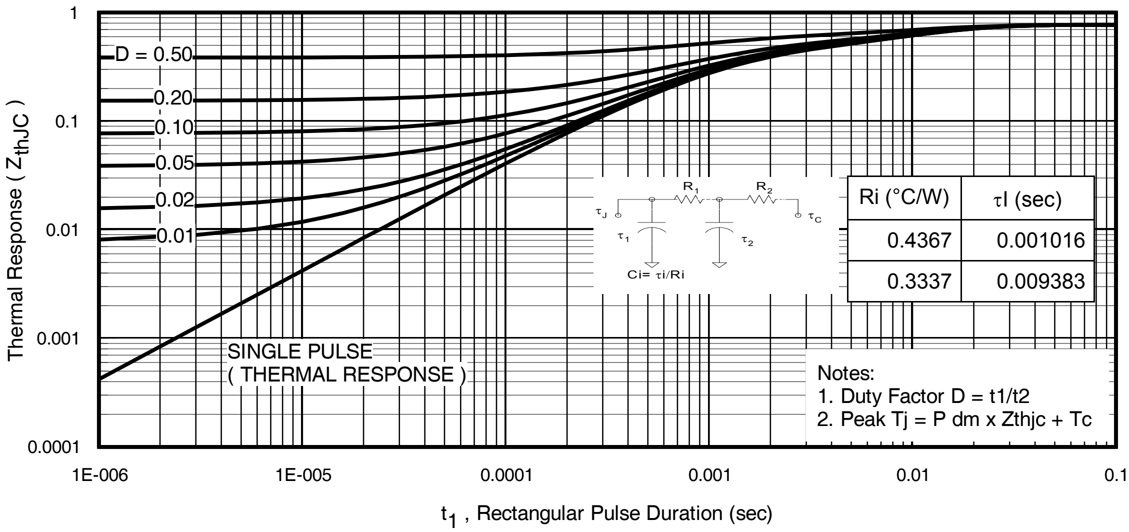


Fig 13. Maximum Effective Transient Thermal Impedance, Junction-to-Case

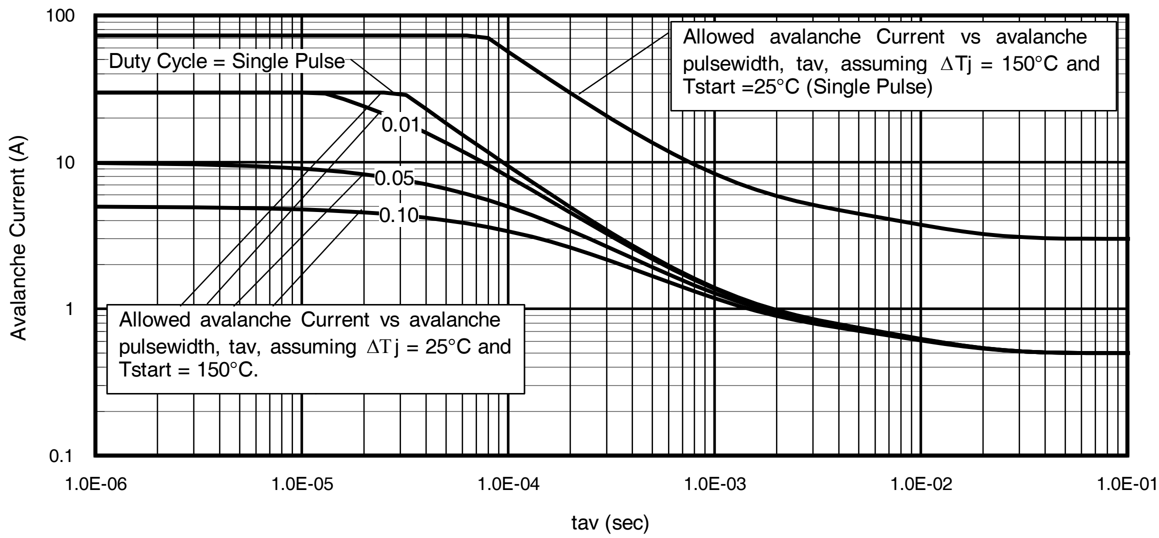


Fig 14. Avalanche Current vs. Pulse width

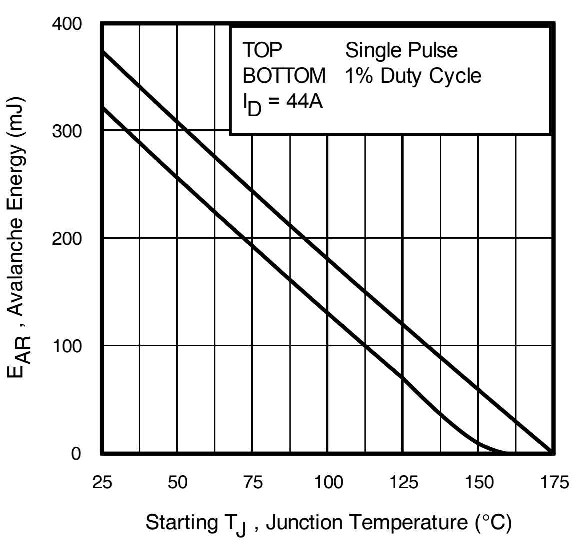


Fig 15. Maximum Avalanche Energy vs. Temperature

Notes on Repetitive Avalanche Curves , Figures 14, 15:
(For further info, see AN-1005 at www.infineon.com)

1. Avalanche failures assumption:
   Purely a thermal phenomenon and failure occurs at a temperature far in excess of T_{jmax}. This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as T_{jmax} is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 18a, 18b.
4. $P_{D\,(ave)}$ = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6. I_{av} = Allowable avalanche current.
7. ΔT = Allowable rise in junction temperature, not to exceed T_{jmax} (assumed as 25°C in Figure 13, 14).
   t_{av} = Average time in avalanche.
   D = Duty cycle in avalanche = $t_{av} \cdot f$
   $Z_{thJC}(D, t_{av})$ = Transient thermal resistance, see Figures 13)

$$P_{D\,(ave)} = 1/2\ (1.3 \cdot BV \cdot I_{av}) = \Delta T / Z_{thJC}$$
$$I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{th}]$$
$$E_{AS\,(AR)} = P_{D\,(ave)} \cdot t_{av}$$

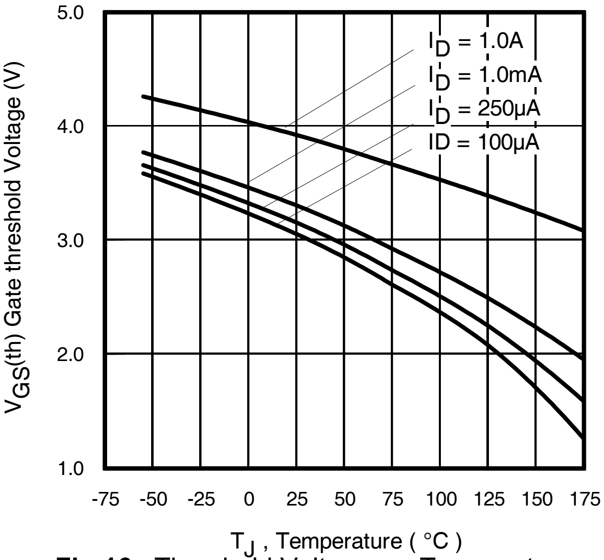


Fig 16. Threshold Voltage vs. Temperature

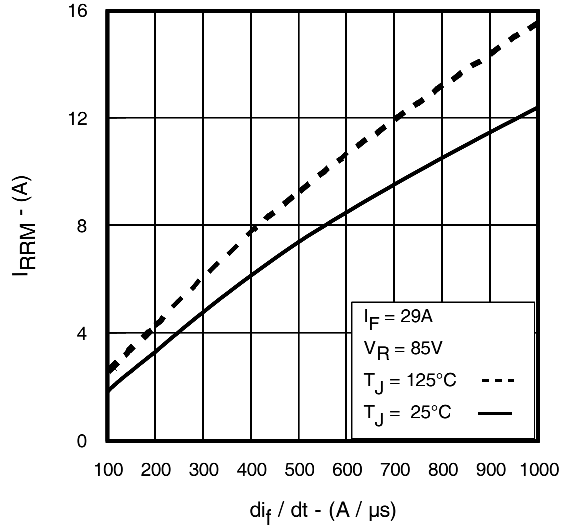


Fig. 17 - Typical Recovery Current vs. dif/dt

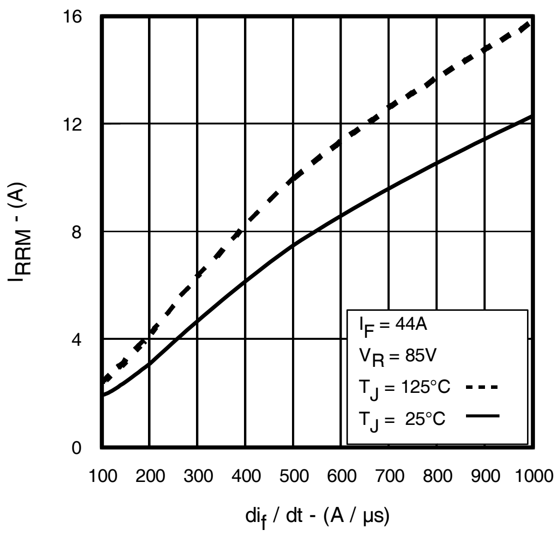


Fig. 18 - Typical Recovery Current vs. dif/dt

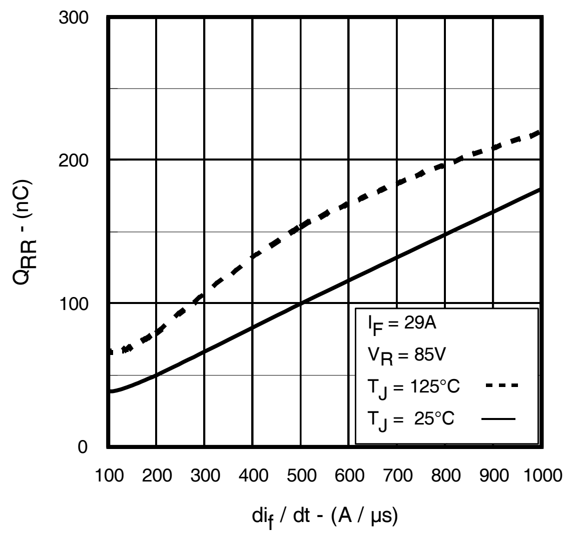


Fig. 19 - Typical Stored Charge vs. dif/dt

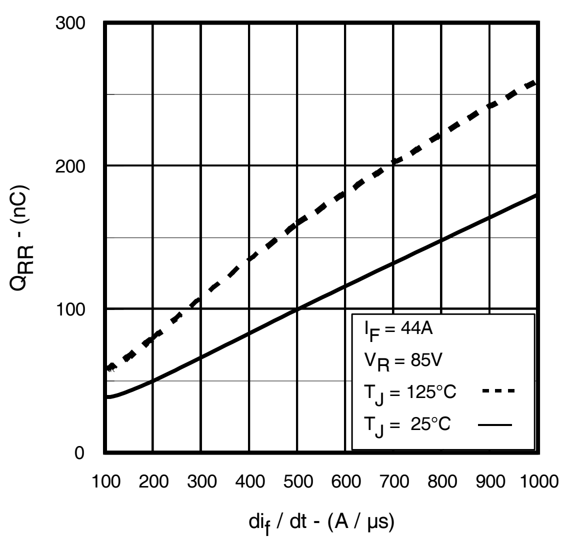


Fig. 20 - Typical Stored Charge vs. dif/dt

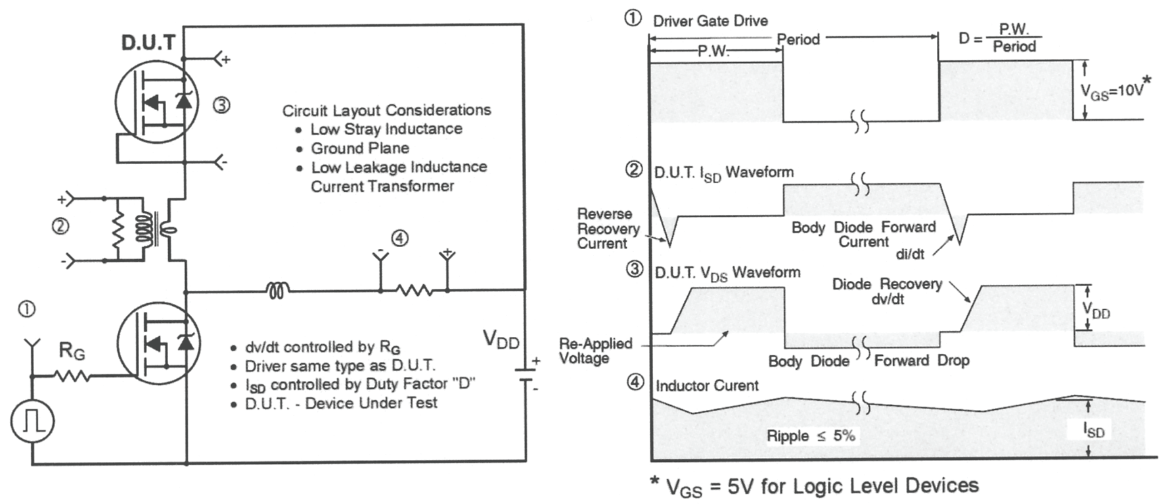


Fig 21. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

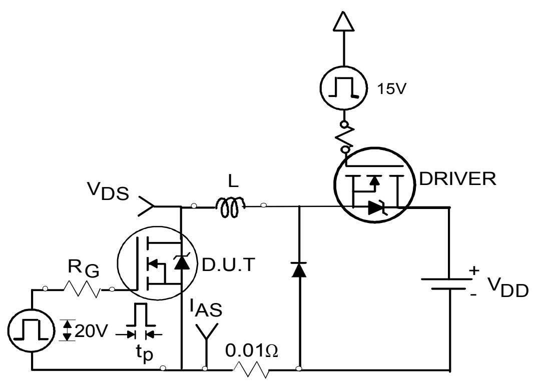


Fig 22a. Unclamped Inductive Test Circuit

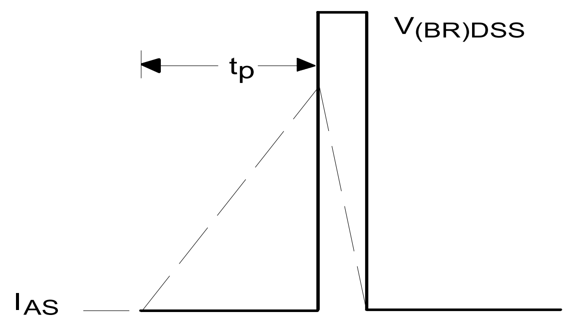


Fig 22b. Unclamped Inductive Waveforms

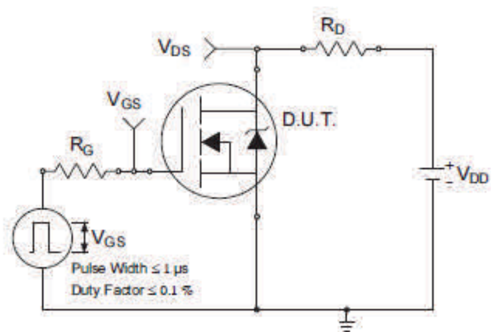


Fig 23a. Switching Time Test Circuit

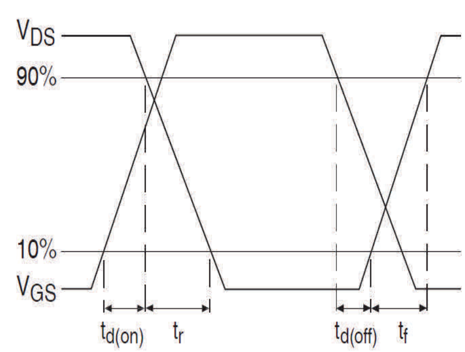


Fig 23b. Switching Time Waveforms

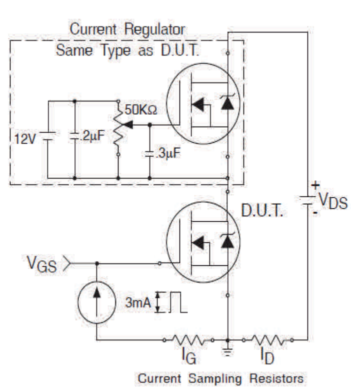


Fig 24a. Gate Charge Test Circuit

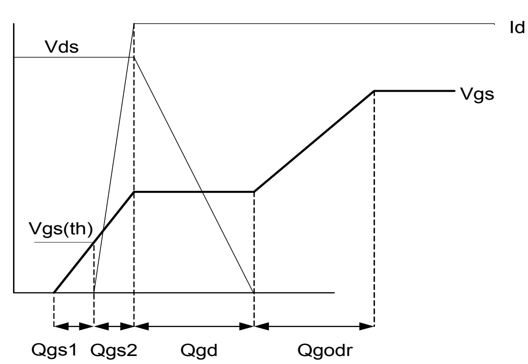
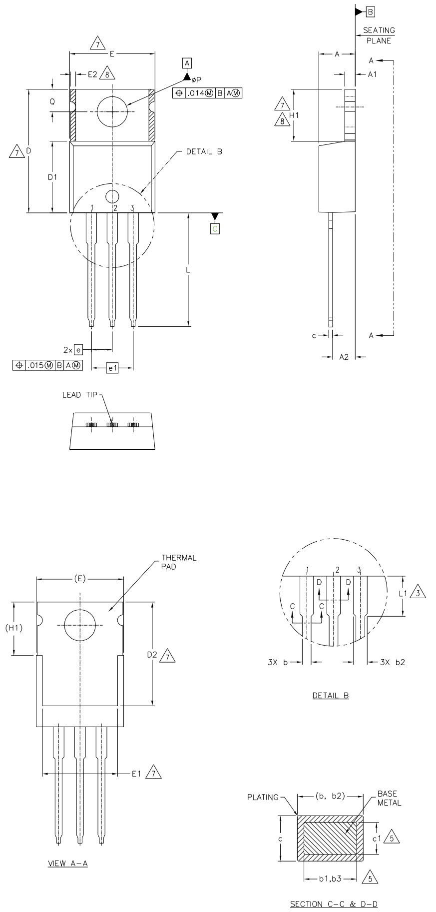


Fig 24b. Gate Charge Waveform

TO-220AB Package Outline (Dimensions are shown in millimeters (inches))



NOTES:

1.– DIMENSIONING AND TOLERANCING AS PER ASME Y14.5 M– 1994.
2.– DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS].
3.– LEAD DIMENSION AND FINISH UNCONTROLLED IN L1.
4.– DIMENSION D, D1 & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5.– DIMENSION b1, b3 & c1 APPLY TO BASE METAL ONLY.
6.– CONTROLLING DIMENSION : INCHES.
7.– THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS E,H1,D2 & E1
8.– DIMENSION E2 X H1 DEFINE A ZONE WHERE STAMPING AND SINGULATION IRREGULARITIES ARE ALLOWED.
9.– OUTLINE CONFORMS TO JEDEC TO-220, EXCEPT A2 (max.) AND D2 (min.) WHERE DIMENSIONS ARE DERIVED FROM THE ACTUAL PACKAGE OUTLINE.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	3.56	4.83	.140	.190	
A1	1.14	1.40	.045	.055	
A2	2.03	2.92	.080	.115	
b	0.38	1.01	.015	.040	
b1	0.38	0.97	.015	.038	5
b2	1.14	1.78	.045	.070	
b3	1.14	1.73	.045	.068	5
c	0.36	0.61	.014	.024	
c1	0.36	0.56	.014	.022	5
D	14.22	16.51	.560	.650	4
D1	8.38	9.02	.330	.355	
D2	11.68	12.88	.460	.507	7
E	9.65	10.67	.380	.420	4,7
E1	6.86	8.89	.270	.350	7
E2	–	0.76	–	.030	8
e	2.54 BSC		.100 BSC		
e1	5.08 BSC		.200 BSC		
H1	5.84	6.86	.230	.270	7,8
L	12.70	14.73	.500	.580	
L1	3.56	4.06	.140	.160	3
ØP	3.54	4.08	.139	.161	
Q	2.54	3.42	.100	.135	

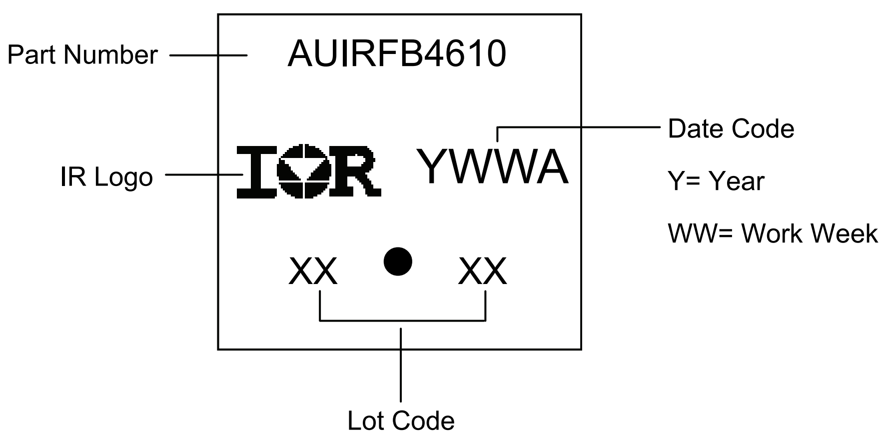
LEAD ASSIGNMENTS

HEXFET
1.– GATE
2.– DRAIN
3.– SOURCE

IGBTs, CoPACK
1.– GATE
2.– COLLECTOR
3.– EMITTER

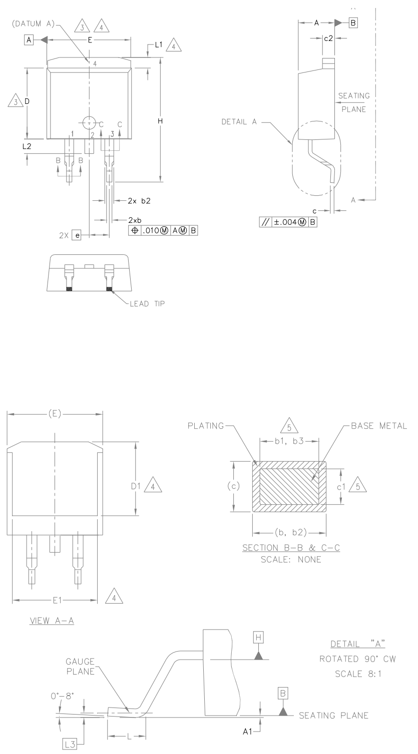
DIODES
1.– ANODE
2.– CATHODE
3.– ANODE

TO-220AB Part Marking Information



Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

D²Pak (TO-263AB) Package Outline (Dimensions are shown in millimeters (inches))



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3. (△3) DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY AT DATUM H.
4. (△4) THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSION E, L1, D1 & E1.
5. (△5) DIMENSION b1, b3 AND c1 APPLY TO BASE METAL ONLY.
6. DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
7. CONTROLLING DIMENSION: INCH.
8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-263AB.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	
A1	0.00	0.254	.000	.010	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	5
b2	1.14	1.78	.045	.070	
b3	1.14	1.73	.045	.068	5
c	0.38	0.74	.015	.029	
c1	0.38	0.58	.015	.023	5
c2	1.14	1.65	.045	.065	
D	8.38	9.65	.330	.380	3
D1	6.86	–	.270	–	4
E	9.65	10.67	.380	.420	3,4
E1	6.22	–	.245	–	4
e	2.54 BSC		.100 BSC		
H	14.61	15.88	.575	.625	
L	1.78	2.79	.070	.110	
L1	–	1.68	–	.066	4
L2	–	1.78	–	.070	
L3	0.25 BSC		.010 BSC		

LEAD ASSIGNMENTS

DIODES

1.– ANODE (TWO DIE) / OPEN (ONE DIE)
2, 4.– CATHODE
3.– ANODE

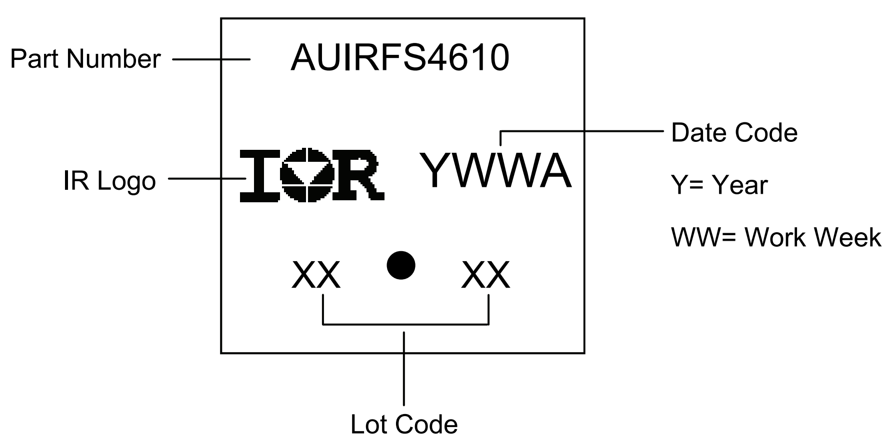
HEXFET

1.– GATE
2, 4.– DRAIN
3.– SOURCE

IGBTs, CoPACK

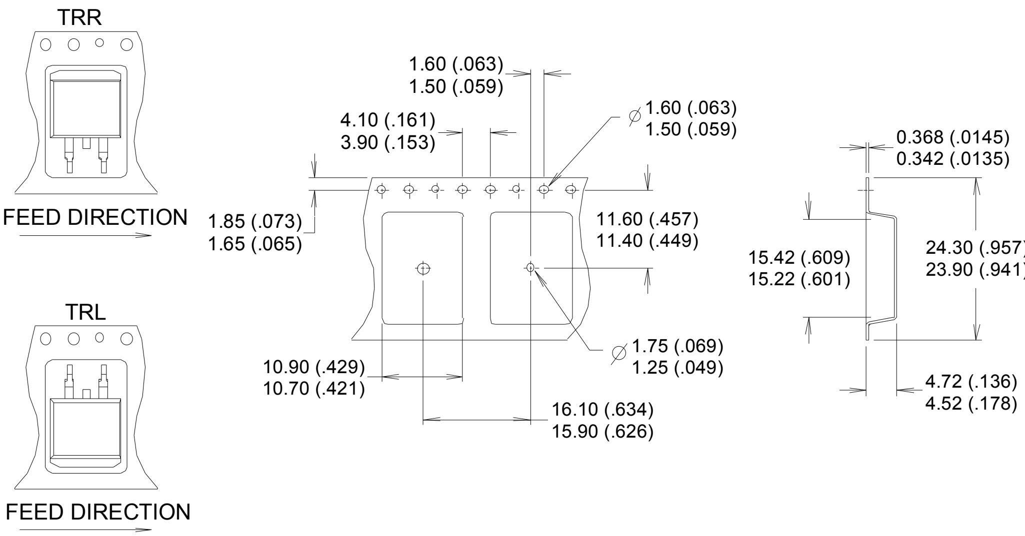
1.– GATE
2, 4.– COLLECTOR
3.– EMITTER

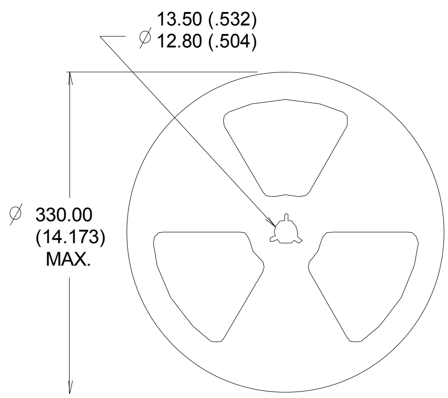
D²Pak (TO-263AB) Part Marking Information

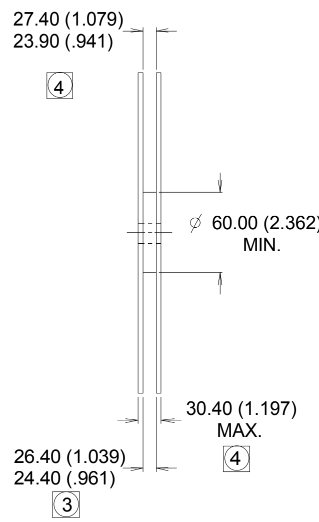


Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

D²Pak (TO-263AB) Tape & Reel Information (Dimensions are shown in millimeters (inches))







NOTES :
1. COMFORMS TO EIA-418.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION MEASURED @ HUB.
4. INCLUDES FLANGE DISTORTION @ OUTER EDGE.

Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

Qualification Information

Qualification Level		Automotive (per AEC-Q101) Comments: This part number(s) passed Automotive qualification. Infineon's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.	
Moisture Sensitivity Level		D^2-Pak	MSL1
		TO-220 Pak	N/A
ESD	Machine Model	Class M4 (+/- 400V)† AEC-Q101-002	
	Human Body Model	Class H1C (+/- 2000V)† AEC-Q101-001	
	Charged Device Model	Class C3 (+/- 750V)† AEC-Q101-005	
RoHS Compliant		Yes	

† Highest passing voltage.

Revision History

Date	Comments
10/27/2015	• Updated datasheet with corporate template • Corrected ordering table on page 1.

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